Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-167-3224

New Online at https://aeiobasegioup.com/hsi//3901-01-107-3224
Inclosure Material:
Ceramic and metal
Overall Length:
0.225 inches
Overall Diameter:
0.127 inches
Mounting Facility Quantity:
1
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded hole
Features Provided:
Hermetically sealed case
Thready Qty Per Inch (tpi):
48
Thread Size:
0.099 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
35.0 breakdown voltage, dc
Current Rating Per Characteristic:
20.00 milliamperes forward current, average peak
Power Rating Per Characteristic:
2.0 watts small-signal input power, common-collector preset
Capacitance Rating In Picofarads:
1.3
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Thread Series Designator:
Terminal Type And Quantity:
1 threaded stud
Shelf Life:
N/a Unit Of Measure:
 Demilitarization:
No
Fiig: A110a0
ATIVAV